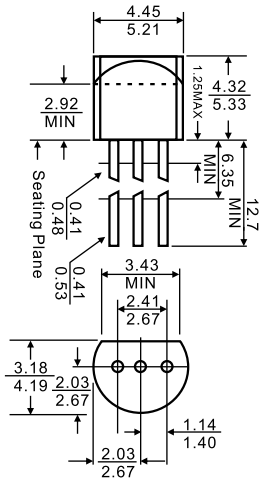
MPS2222A

TO-92 Transistor (NPN)

1. EMITTER
2. BASE
3. COLLECTOR

TO-92



Dimensions in inches and (millimeters)

Features

✧ **Complementary NPN Type available (MPS2907A)**

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	75	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	600	mA
P_C	Collector Power Dissipation	625	mW
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= 10uA , I_E=0	75		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= 10mA , I_B=0	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= 10uA, I_C=0	6		V
Collector cut-off current	I_{CBO}	V_{CB}= 60V, I_E=0		10	nA
Collector cut-off current	I_{CEX}	V_{CE}= 60V,$V_{EB(Off)}$=3V		10	nA
Emitter cut-off current	I_{EBO}	V_{EB}= 3 V, I_C=0		100	nA
DC current gain	$h_{FE(1)}$	V_{CE}=10V,I_C= 150mA	100	300	
	$h_{FE(2)}$	V_{CE}=10V,I_C= 0.1mA	40		
	$h_{FE(3)}$*	V_{CE}=10V, I_C= 500mA	42		
Collector-emitter saturation voltage	$V_{CE(sat)(1)}$*	I_C= 500mA, I_B=50mA		0.6	V
	$V_{CE(sat)(2)}$*	I_C= 150mA, I_B=15mA		0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$*	I_C= 500mA, I_B= 50mA		1.2	V
Delay time	t_d	V_{CC}=30V, $V_{EB(Off)}$=-0.5V,		10	nS
Rise time	t_r	I_C=150mA,I_{B1}=15mA		25	nS
Storage time	t_S	V_{CC}=30V,Ic=150mA,I_{B1}=I_{B2}=15mA		225	nS
Fall time	t_f			60	nS
Transition frequency	f_T	V_{CE}=20V, I_C=20mA, f=100MHz	300		MHz

*pulse test

CLASSIFICATION OF $h_{FE(1)}$

Rank	L	H
Range	100-200	200-300

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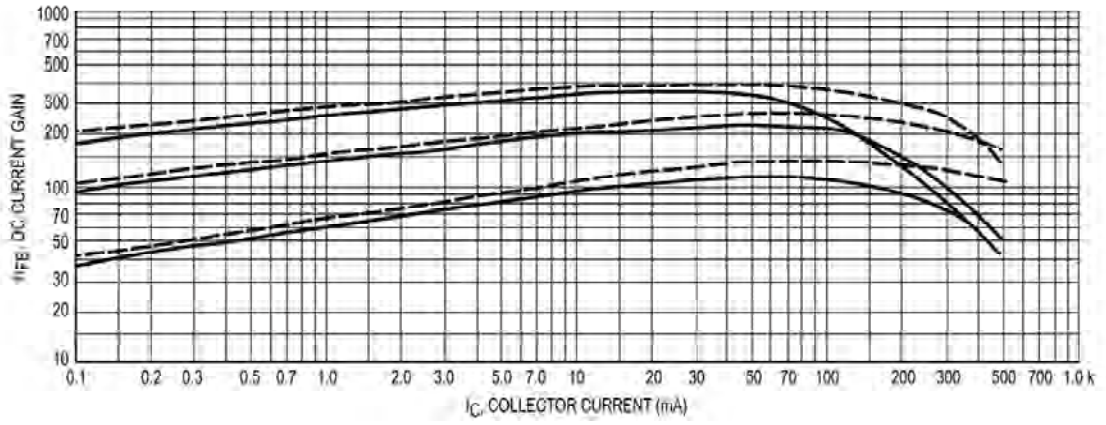
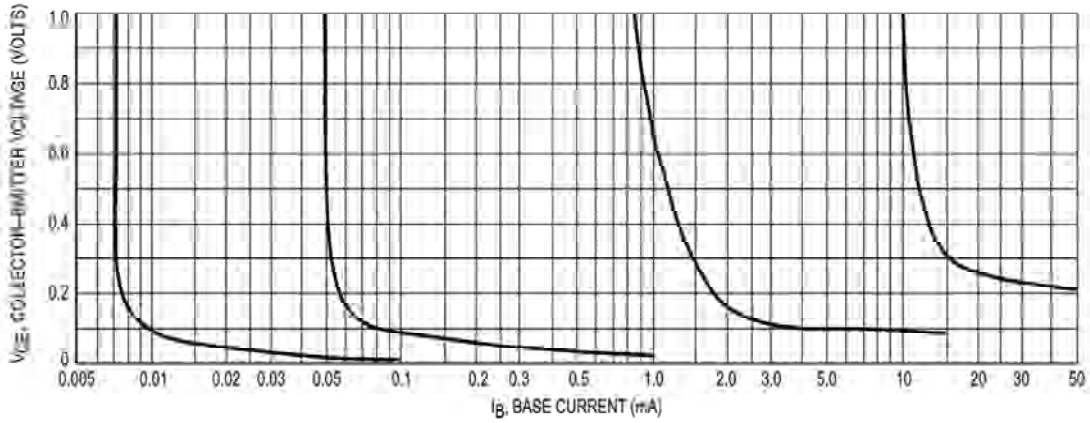
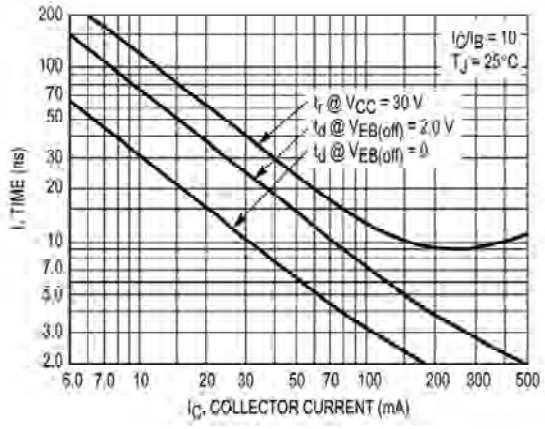
Typical characteristics



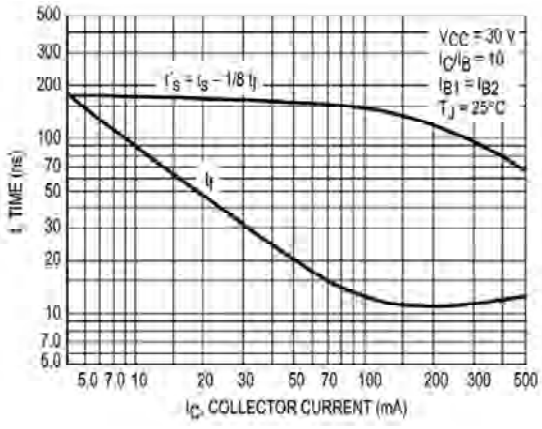
DC Current Gain



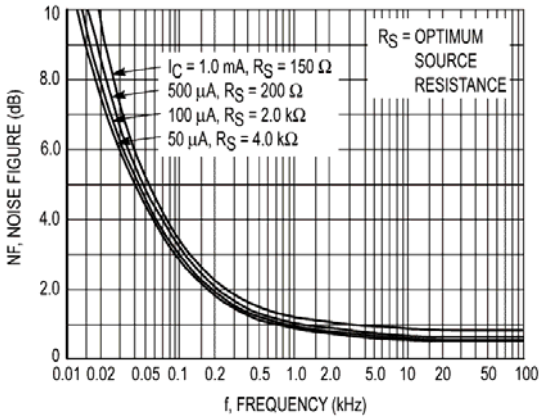
Collector Saturation Region



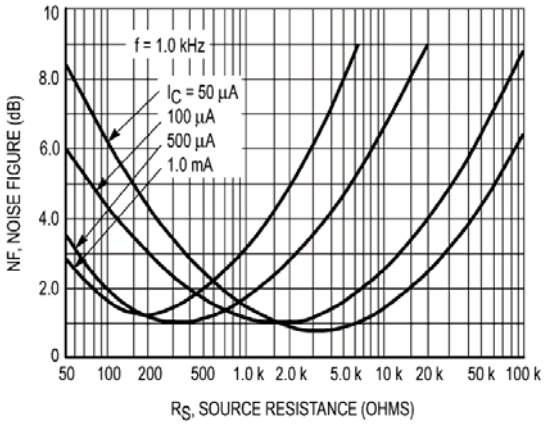
Turn–On Time



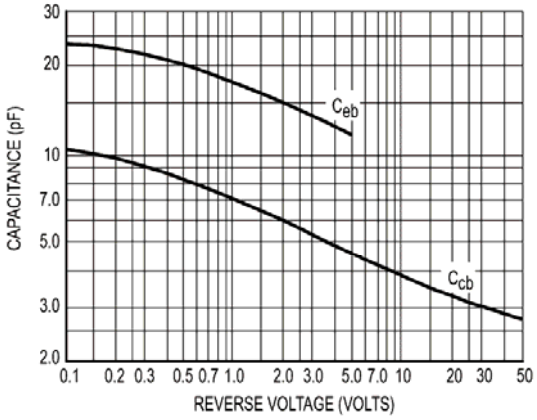
Turn–Off Time



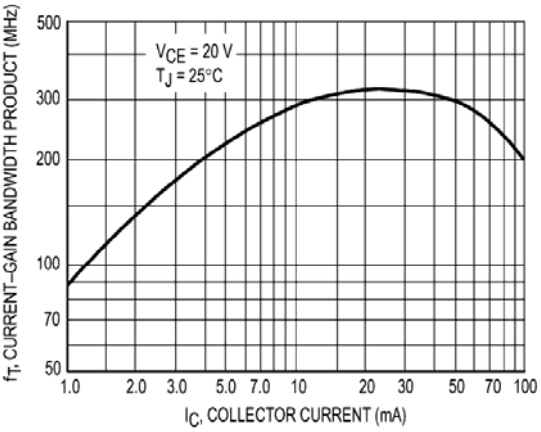
Frequency Effects



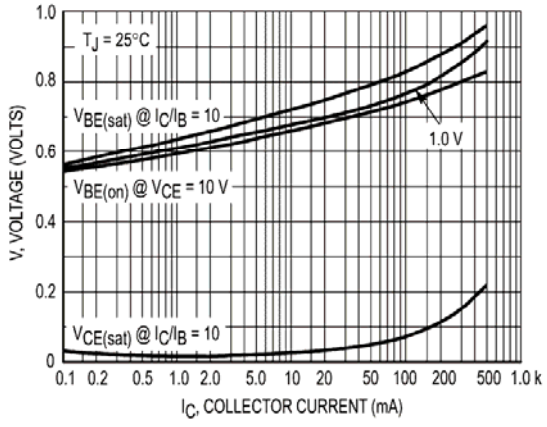
Source Resistance Effects



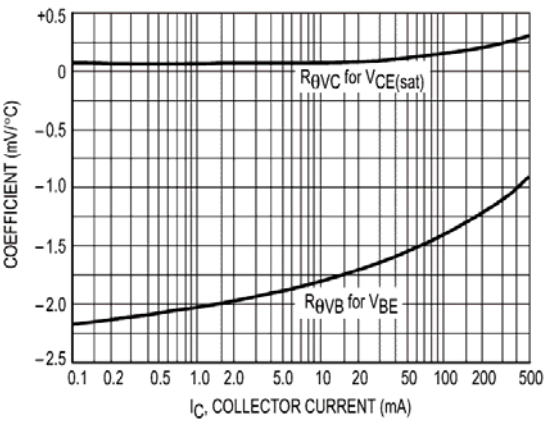
Capacitances



Current–Gain Bandwidth Product



"On" Voltages



Temperature Coefficients

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